# SUMMER- 18 EXAMINATION 

Subject Name: Principles of Digital Techniques
Model Answer

## Important Instructions to examiners:

1) The answers should be examined by key words and not as word-to-word as given in the model answer scheme.
2) The model answer and the answer written by candidate may vary but the examiner may try to assess the understanding level of the candidate.
3) The language errors such as grammatical, spelling errors should not be given more Importance (Not applicable for subject English and Communication Skills.
4) While assessing figures, examiner may give credit for principal components indicated in the figure. The figures drawn by candidate and model answer may vary. The examiner may give credit for any equivalent figure drawn.
5) Credits may be given step wise for numerical problems. In some cases, the assumed constant values may vary and there may be some difference in the candidate's answers and model answer.
6) In case of some questions credit may be given by judgement on part of examiner of relevant answer based on candidate's understanding.
7) For programming language papers, credit may be given to any other program based on equivalent concept.

| $\begin{array}{\|l\|} \hline \text { Q. } \\ \text { No. } \end{array}$ | $\begin{aligned} & \text { Sub } \\ & \text { Q. N. } \end{aligned}$ | Answers | Marking Scheme |
| :---: | :---: | :---: | :---: |
| 1 | a | Attempt any six: | 12-Total Marks |
|  | i | Convert (AC) H into binary and octal. | 2M |
|  | Ans: | 1) $\begin{aligned} (\mathrm{AC})_{H} & =(?)_{2}=(?)_{8} \\ & =(10101100)_{2} \end{aligned}$ <br> 2) $(\mathrm{AC})_{\mathrm{H}}=\begin{array}{ll}\frac{(10}{\downarrow} & \frac{101}{\downarrow} \\ 2 & 5\end{array}$ | $\begin{aligned} & 1 \mathrm{M} \\ & 1 \mathrm{M} \end{aligned}$ |
|  | ii | Draw symbol, Truth table and logical equation of Ex-OR gate. | 2M |
|  | Ans: | Symbol | $1 / 2 \mathrm{M}$ $1 / 2 \mathrm{M}$ |

## SUMMER- 18 EXAMINATION



## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer

|  |  |  |
| :---: | :---: | :---: |
| v | Specify the function of - <br> 1) IC 74245 : <br> 2) IC 74151 : | 2M |
| Ans: | 1) IC 74245: Octal Bus Transceiver <br> a) It is octal bidirectional buffer IC <br> b) It is used as a driver for the data bus <br> c) Total 16 bus drivers, 8 for each direction with tristate output <br> d) The direction of data flow is controlled by DIR pin <br> 2) IC 74151: 8:1 Multiplexer <br> a) It has 8 inputs and 1 output <br> b) $2^{N}=8, N=3$ select lines, whose bit combination determines which combination is selected at output | 1M <br> (Minimum <br> One function) <br> 1M <br> (Minimum <br> One function) |
| vi | What is Flash memory? | 2M |
| Ans: | 1. Flash Memory is nonvolatile RAM memory <br> 2. It can be Electrically erased and reprogrammed <br> 3. Flash memory can be written into blocks size rather than byte. It is easy to update. <br> 4. It is faster than EEPROM as EEPROM edit the data at Byte level. <br> 5. As large block of data can be erased at one time (or flash)thus called as flash | (Any 4 points) $1 / 2 \mathrm{M}$ each |

## SUMMER- 18 EXAMINATION

memory.
6. Features: High speed, low operating voltage and low power consumption
7. Applications: 1. Cellular phone
2. Digital camera's embedded controller.

|  | memory. <br> 6. Features: High speed, low operating voltage and low power consumption <br> 7. Applications: 1. Cellular phone <br> 2. Digital camera's embedded controller. |  |
| :---: | :---: | :---: |
| vii | Write applications of DAC and ADC. | 2M |
| Ans: | 1. In Process control system <br> 2. Low power converter for remote data acquisition <br> 3. Battery operated equipment <br> 4. Acquisition of analog values in automotive, audio and TV application <br> (Any suitable relevant application should be considered) | $\begin{aligned} & 1 \mathrm{M}(\text { Any } \\ & \text { two) } \end{aligned}$ |
| viii | List advantages of TTL logic family. | 2M |
| Ans: | 1. Low propagation delay, hence TTL circuits are fast. <br> 2. Power dissipation is independent of Frequency. <br> 3. No latch ups. <br> 4. TTL is compatible to other logic families. <br> 5. High current sourcing and sinking capabilities. <br> (Relevant advantages should be considered) | $1 / 2 \mathrm{M}$ each (any 4) |
| b | Attempt any TWO: | 08-Total Marks |
| i | Perform binary subtraction using 2's complement method. $(12)_{10}-(08)_{10}$ | 4M |

## SUMMER- 18 EXAMINATION

| Ans: | 1. Finding equivalent binary for $(12)_{10}$ and $(08)_{10}$ $\begin{aligned} & (12)_{10}=(1100)_{2} \\ & (08)_{10}=(1000)_{2} \end{aligned}$ <br> 2. Taking 1 's complement of $(1000)_{2}$ <br> 1's complement of 1000 => 0111 <br> 3. Adding (12) $)_{10}$ and 2 's complement of ( 08$)_{10}$ <br> 4. If carry comes discard carry <br> 5. Answer is positive and in real form $=(0100)_{2}=(04)_{10}$ | 1M <br> 1 M <br> 1M <br> 1M |
| :---: | :---: | :---: |
| ii | Convert following expression into canonical SOP form $Y=A+B C+A B C$ | 4M |
| Ans: | $\begin{array}{ll} \mathrm{Y}=\mathrm{A}+\mathrm{BC}+\mathrm{ABC} & \\ =A .1 .1+B C .1+A B C & \text { Multiplying each sum by missing term } \\ =A(B+\bar{B})(C+\bar{C})+B C(A+\bar{A})+A B C & \text { As }(B+\bar{B})=1 \end{array}$ | 1M For each step |

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer
Subject Code:
17320


## SUMMER- 18 EXAMINATION



## SUMMER- 18 EXAMINATION




## SUMMER- 18 EXAMINATION



## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer
Subject Code:
17320



| $\begin{array}{l\|l} \text { Q. } \end{array}$ | Sub <br> Q. <br> N. | Answers | Marking Scheme |
| :---: | :---: | :---: | :---: |
| 3 |  | Attempt any FOUR: | 16-Total Marks |
|  | a | Minimize the following expression using k-map and realize it using basic logic gates. $Y=\sum m(1,3,4,5,6,7)$ | 4M |
|  | Ans: |  | $2 \mathrm{M}-\mathrm{K}-$ <br> map \& 2M <br> Realization |

## SUMMER- 18 EXAMINATION



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Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer

| Ans: | Circuit Diagram: <br> Operation: <br> - Manual RESET, will reset ramp generator as well as counter.VA has to be positive. RAMP begins at $0 V$. <br> - As VAX < VA, VC = 1 (HIGH). This will enable CLOCK gate allowing the CLK input, to be applied to the counter. <br> - As counter receives clock pulses, it will count up; and the RAMP continues upward. <br> - RAMP voltage rises till it reaches to VA input voltage. <br> - At this point, time t1, output $\mathrm{V}_{0}=0$ (LOW) and it will disable CLOCK gate and counter cease to advance. <br> - The negative transition of $\mathrm{V}_{0}$, simultaneously generates a strobe signal in the CONTROL box that shifts the contents of the three decade counters into the three 4 FF latch circuit. <br> - Shortly after that, a reset pulse is generated (time t2), by the CONTROL box that resets the RAMP and clears the decade counter to all O's (ZEROS) and another conversion cycle begins. | 2M - Circuit <br>  <br> 2M- <br> Explanation |
| :---: | :---: | :---: |

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer

|  | - In th latch | the meantime the cont <br> hes and are displayed | nts of the previous <br> on the seven segmen | onversion are containe t display. |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
| f | Differentiat <br> (i) <br> (ii) | te between <br> Static RAM and dy <br> Volatile and Non- | namic RAM <br> olatile memory |  | 4M |
| Ans: | (i) | Static RAM and dynamic RAM |  |  | 2M each <br> (Any 2 points) |
|  |  | Parameter | Static RAM | Dynamic RAM |  |
|  |  | Circuit Configuration | Each SRAM cell is a flip flop | Each cell is one <br> MOSFET \& a capacitor |  |
|  |  | Bits stored | In the form of voltage | In the form of charges |  |
|  |  | No. of components per cell | More | Less |  |
|  |  | Storage capacity | Less | More |  |
|  | (ii) | ) Volatile and Non-Volatile memory |  |  |  |
|  |  | Parameter | Volatile memory | Non-Volatile memory |  |
|  |  | Definition | Information is if power is turned off | Information is not lost if power is turned off |  |
|  |  | Classification | All RAMs | ROMs, EPROM, magnetic memories |  |
|  |  | Effect of power | Stored information is retained only as long as power is on | No effect of power on stored information |  |
|  |  | Applications | For temporary storage | For permanent storage of information. |  |

SUMMER- 18 EXAMINATION
Subject Name: Principles of Digital Techniques
Model Answer

| $\begin{aligned} & \text { Q. } \\ & \text { No. } \end{aligned}$ | $\begin{aligned} & \text { Sub } \\ & \text { Q. } \\ & \mathrm{N} . \end{aligned}$ | Answers | Marking Scheme |
| :---: | :---: | :---: | :---: |
| 4 |  | Attempt any FOUR: | 16-Total Marks |
|  | a | (i) Add binary numbers. $(10110.110)_{2}+(1001.1)_{2}$ <br> (ii) Multiply $(1110)_{2} \times(101)_{2}$ | 4M |
|  | Ans: |  | 2M 2M |
|  | b | Realize the following expression using only NOR gate. $\mathrm{Y}=(\mathrm{ABC}+\overline{\mathrm{B}}+\overline{\mathrm{C}}) \cdot \mathrm{C}$ | 4M |

## SUMMER- 18 EXAMINATION

Ans:

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer
Subject Code:
17320


## SUMMER- 18 EXAMINATION

|  |  <br>  $\begin{aligned} & \mathrm{J} 0=\mathrm{K} 0=1 \\ & \mathrm{~J} 1=\mathrm{K} 1=\mathrm{Q} 0 \\ & \mathrm{~J} 2=\mathrm{K} 2=\mathrm{Q} 1 * \mathrm{Q} 2 \end{aligned}$ <br> Step 3: <br> Draw the complete design as below: <br> Note : It can also be designed using T Flip Flop. |  |
| :---: | :---: | :---: |
| e | Draw single digit memory cell using NAND gates and explain working with truth table. | 4M |

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer
Subject Code:
17320


## SUMMER-18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer
Subject Code:
17320

| Q. <br> No. | Sub <br> Q. <br> N. | Answers | Marking Scheme |  |
| :--- | :--- | :--- | :--- | :--- |
| 5 |  | Attempt any FOUR: |  |  |
|  | a | Compare single slope ADC and dual slope ADC (any four points). | 16-Total Marks |  |
|  |  |  |  |  |

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER- 18 EXAMINATION

1) RAM :

- Random access memory is also called as read-write memory.
- In this type of memories, the memory locations are organized in such a way that the access time required for any location is same.
- Data stored at any location can be changed during the operation of the system.


## 2) Static RAM

- This type of memory can be implemented by bipolar as well as MOS technology.
- It is possible to store data as long as power is applied to the chip.
- The basic cell in SRAM is a flip-flop


## 3) Dynamic RAM

- In dynamic RAM, the data is stored in the form of charge on the capacitor.
- Its formed using MOSFET and capacitor.
- It needs to be refreshed after every few milliseconds.


## 4) Flash Memory:-

- Flash memory is non-volatile RAM memory that can be electrically erased and reprogrammed.
- Flash memory can be written to in block size rather than byte, it is easier to update it.
- Due to this, the flash memories are faster than EEPROMS which erase and
write new data of byte level.
- This type of memory has been named as 'flash memory' because a large block of memory could be erased at one time, i.e. in a single action or 'flash'.
- Important features are high speed, low operating voltages, low power consumption.
- Typical application areas are digital camera`s embedded controllers, cellular phones etc.


## 5) Programmable Read Only Memories (PROM):-

- PROM is electrically programmable i.e. the data pattern is defined after final packaging rather than when the device is fabricated.
- The programming is done with an equipment referred to as PROM programmer.
- The PROM are one time programmable. Once programmed, the information stored is permanent.

6) Erasable Programmable Read Only Memories (EPROM):-

- In these memories, data can be written in any number of times i.e. they are reprogrammable.
- Reprogrammable ROMs are possible only in MOS technology. For erasing the contents of the memory, one of the following two methods are employed:
a) Exposing the chip to ultraviolet radiation for about 30minutes (UVEPROM)
b) Erasing electrically by applying voltage of proper polarity \& amplitude.

Electricity
erasable Prom is also referred to as E²PROM or EEPROM or EAROM (Electrically alterable ROM)

Why NAND and NOR gates are called as universal gates. Derive basic gates using NOR gates only.

## SUMMER-18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER-18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer
Subject Code: 17320


Ans: Truth Table for 4 bit Binary to Gray code converter

| Binary Input |  |  |  | Gray Output |  |  |  |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{B}_{3}$ | $\mathrm{~B}_{2}$ | $\mathrm{~B}_{1}$ | $\mathrm{~B}_{0}$ | $\mathrm{G}_{3}$ | $\mathrm{G}_{2}$ | $\mathrm{G}_{1}$ | $\mathrm{G}_{0}$ |
| 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 0 | 0 | 0 | 1 | 0 | 0 | 0 | 1 |
| 0 | 0 | 1 | 0 | 0 | 0 | 1 | 1 |
| 0 | 0 | 1 | 1 | 0 | 0 | 1 | 0 |
| 0 | 1 | 0 | 0 | 0 | 1 | 1 | 0 |
| 0 | 1 | 0 | 1 | 0 | 1 | 1 | 1 |
| 0 | 1 | 1 | 0 | 0 | 1 | 0 | 1 |
| 0 | 1 | 1 | 1 | 0 | 1 | 0 | 0 |
| 1 | 0 | 0 | 0 | 1 | 1 | 0 | 0 |
| 1 | 0 | 0 | 1 | 1 | 1 | 0 | 1 |
| 1 | 0 | 1 | 0 | 1 | 1 | 1 | 1 |
| 1 | 0 | 1 | 1 | 1 | 1 | 1 | 0 |
| 1 | 1 | 0 | 0 | 1 | 0 | 1 | 0 |
| 1 | 1 | 0 | 1 | 1 | 0 | 1 | 1 |
| 1 | 1 | 1 | 0 | 1 | 0 | 0 | 1 |
| 1 | 1 | 1 | 1 | 1 | 0 | 0 | 0 |

K-MAP FOR G3:

## SUMMER- 18 EXAMINATION



K-MAP FOR G2:


Equation for $\mathrm{G} 2=\overline{\mathrm{B} 3} \mathrm{~B} 2+\mathrm{B} 3 \overline{\mathrm{~B} 2}=\mathrm{B} 3$ XOR B2

K-MAP FOR G1:


Equation for $\mathrm{G} 1=\overline{\mathrm{B} 1} \mathrm{~B} 2+\mathrm{B} 1 \overline{\mathrm{~B} 2}=\mathrm{B} 1$ XOR B 2

K-MAP FOR GO:

## SUMMER- 18 EXAMINATION



Equation for $\mathrm{GO}=\overline{\mathrm{B} 1} \mathrm{BO}+\mathrm{B} 1 \overline{\mathrm{~B} 0}=\mathrm{B} 1$ XOR BO
Diagram for 4 bit Binary to Gray code converter


## OR

Diagram for 3 bit Binary to Gray code converter (2 Mks)


Truth Table for 3 bit Binary to Gray code converter (2 Mks)

| Binary Input |  |  |  | Gray Output |  |  |  |
| :--- | :--- | :--- | :--- | :--- | :--- | :---: | :---: |
| $\mathrm{B}_{2}$ | $\mathrm{~B}_{1}$ | $\mathrm{~B}_{0}$ | $\mathrm{G}_{2}$ | $\mathrm{G}_{1}$ | $\mathrm{G}_{0}$ |  |  |
| 0 | 0 | 0 | 0 | 0 | 0 |  |  |
| 0 | 0 | 1 | 0 | 0 | 1 |  |  |
| 0 | 1 | 0 | 0 | 1 | 1 |  |  |



## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER-18 EXAMINATION



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SUMMER- 18 EXAMINATION

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Subject Name: Principles of Digital Techniques
Model Answer
Subject Code:

| $\begin{aligned} & \mathrm{Q} . \\ & \text { No. } \end{aligned}$ | $\begin{aligned} & \text { Sub } \\ & \text { Q. N. } \end{aligned}$ | Answers | Marking Scheme |
| :---: | :---: | :---: | :---: |
| 6 |  | Attempt any FOUR: | 16-Total Marks |
|  | A | Draw the pinout configuration for <br> (i) 1 C 7402 <br> (ii)IC 7404 | 4M |
|  | Ans: | Pin Diagram of IC 7402 <br> Pin Diagram of IC 7404 | $2 \mathrm{M}$ $2 \mathrm{M}$ |
|  | B | Implement 1:16 Demux using 1:4 Demux write a truth table. | 4M |

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


## SUMMER-18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer


| Ans: | Explanation- <br> IC 74181 is a high speed, 24 pin IC DIL package. Widely used combinational logic, capable of performing the arithmetic as well as logical operations. It is the heart of microprocessor. $A$ and $B$ are the two 4 bit input variables, <br> $F$ is the 4 bit output variable, $S$ are the 4 bit select lines that decides various (either arithmetic or logical) operations <br> $M=$ mode control that decides whether ALU will perform arithmetic or logical operations If $M=1,16$ Logical operations (AND,OR ,NOR etc operations, depending upon the 4 bit combination of select lines) <br> If $\mathrm{M}=0,16$ Arithmetic operations ( addition, subtraction, division etc operations ,depending upon the 4 bit combination of select lines) <br> $A=B$,Comparator equality output <br> $G$ and $P$ are the carry generate and carry propagate outputs used for cascading of ALUs | Diagram 2M <br> Explanation <br> 2 mks |
| :---: | :---: | :---: |
| f | Calculate output voltage for 4 bit binary weighted resistor DAC for binary inputs and $V_{\text {ref }}=5 \mathrm{~V}$. <br> (i) 1010 <br> (ii i) 1100 | 4M |

## SUMMER- 18 EXAMINATION

Subject Name: Principles of Digital Techniques
Model Answer

Ans: $\quad$ Considering MSB resistor is $2 R, R_{F}=R$
Output voltage for 4 bit (D C B A) binary weighted resistor DAC is given by $V o=\frac{R F}{R}$ Vref $\left(\frac{b_{n-1}}{2^{1}}+\frac{b_{n-1}}{2^{2}}+\frac{b_{n-1}}{2^{3}}+\frac{b_{n-1}}{2^{4}}\right)$
(i) $1010=\mathrm{DCBA}$
$V o=\operatorname{Vref}\left(\frac{1}{2^{1}}+\frac{0}{2^{2}}+\frac{1}{2^{3}}+\frac{0}{2^{4}}\right)$
$=3.125 \mathrm{~V}$
(ii) $1100=\mathrm{DCBA}$
$V o=V$ ref $\left(\frac{1}{2^{1}}+\frac{1}{2^{2}}+\frac{0}{2^{3}}+\frac{0}{2^{4}}\right)$
$=3.75 \mathrm{~V}$
(OR)
Considering $\mathrm{V}(0)=0 \mathrm{~V}$ and $\mathrm{V}(1)=\mathrm{V}_{\text {ref }}=5 \mathrm{~V}$
MSB resistor is $2 R, R_{f}=R$
output voltage for 4 bit (D C B A) binary weighted resistor DAC is given by

$$
V_{0}=\left[\frac{V_{D}}{2}+\frac{V_{C}}{4}+\frac{V_{B}}{8}+\frac{V_{A}}{16}\right]
$$

Where $\mathrm{D}=\mathrm{MSB}$ bit \& $\mathrm{A}=\mathrm{LSB}$ bit
(iii i) $1010=\mathrm{DCBA}$

$$
\begin{aligned}
& V_{0}=\left[\frac{5}{2}+\frac{0}{4}+\frac{5}{8}+\frac{0}{16}\right] \\
& V_{0}=3.125 \mathrm{~V}
\end{aligned}
$$

Note :- Mark should be given even if MSB resistor is taken as R and calculated using formula,

$$
V_{o}=V_{D}+\frac{V_{C}}{2}+\frac{V_{B}}{4}+\frac{V_{A}}{8}
$$

